

REMARKS

Claim 37 has been amended. No claims have been canceled or added. Accordingly, claims 37-41 are currently pending in the application, of which, claims 38-40 have been withdrawn from consideration.

35 U.S.C. §112

Claim 37 has been amended to overcome the outstanding rejection under 35 U.S.C. §112.

35 U.S.C. §103

Claims 37 and 41 stand rejected under 35 U.S.C. §103 as being unpatentable over Yano et al. This rejection is traversed as follows.

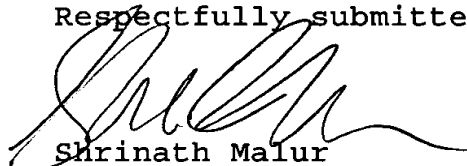
The present invention is directed to a semiconductor memory apparatus in which different information can be written into a charged storage node by applying different voltages to the source-drain region. In a memory cell driven by the same word line, a large voltage is applied between the source and drain to set the threshold voltage large, and a small voltage is applied between the source and drain to set the threshold voltage small. This feature of the present invention is

neither disclosed nor suggested by Yano et al. In other words, Yano et al do not disclose or suggest writing different information by applying a different voltage between the source and drain in the case of a memory device storing a small number of electrons in a small storage region. In fact, Applicants believe that such a writing operation has not been known prior to this invention in connection with a single electron memory or small electron memory device.

CONCLUSION

In view of the foregoing amendments and remarks, Applicants contend that the above-identified application is now in condition for allowance. Accordingly, reconsideration and reexamination are respectfully requested.

Respectfully submitted,



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